Abstracts

A 6 Watt Power GaAs FET for 14.0-14.5GHz Band

Y. Kadowaki, S. Igi, M. Wataze, T. Sonoda, K. Hayashi, M. Yamanouchi, S. Takamiya and S. Mitsui. "A 6 Watt Power GaAs FET for 14.0-14.5GHz Band." 1987 MTT-S International Microwave Symposium Digest 87.2 (1987 Vol. II [MWSYM]): 845-847.

An internally matched GaAs FET with output power above 38dBm(6.3W) and linear power gain above 5.8dB has been developed for the 14.0-14.5GHz band. These results were achieved by using high quality GaAs wafers prepared by molecular beam epitaxy (MBE) and optimizing the channel recess structure. Additionally, the package size of the FET was successfully reduced by using a high dielectric substrate for the internal matching circuits of both input and output.

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